

Please amend the Abstractd as follows.

**ABSTRACT OF THE DISCLOSURE**

~~The present invention describes in detail the construction and operation of a~~ A CMOS Active Pixel Image Sensor ~~that consists of pixels~~ is formed by only two transistors. The sensor ~~can~~ may be fabricated with very small pixel sizes, which have only two metal contacts in them, have in-pixel offset non-uniformity correction, and bootstrapped reset lines. These features are achieved by employing the transistor body effect as the main photo-generated charge sensing means. The bootstrapped reset lines allow the sensor to operate at low bias voltages. Additional embodiments of the invention include: single line for addressing the pixels, column-clamping circuits to prevent the forward biasing of pixel's p-n junctions and trench isolation to minimize the pixel size.

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